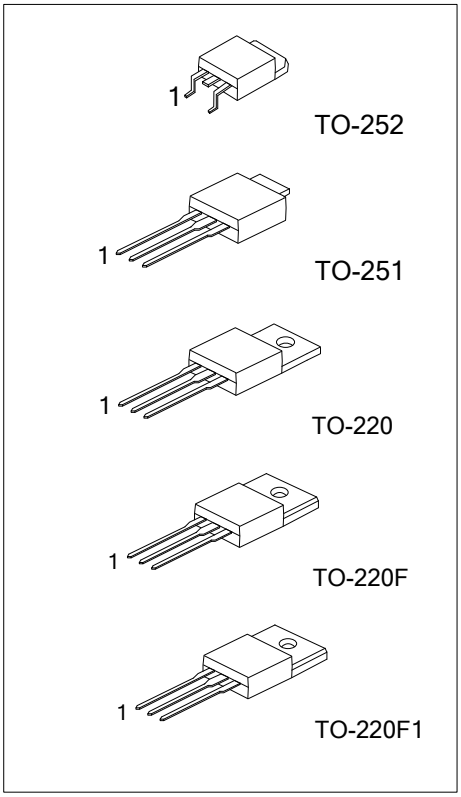
5N60

Power MOSFET

4.5 Amps, 600/650 Volts N-CHANNEL MOSFET



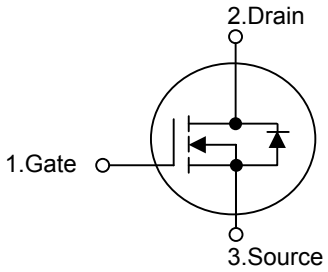
■ DESCRIPTION

The UTC **5N60** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

* $R_{DS(ON)}$ = 2.5Ω @V_{GS} = 10 V
* Ultra Low Gate Charge (Typical 15 nC)
* Low Reverse Transfer Capacitance (C_{RSS} = Typical 6.5 pF)
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, High Ruggedness

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
5N60L-x-TA3-T	5N60G-x-TA3-T	TO-220	G	D	S	Tube
5N60L-x-TF3-T	5N60G-x-TF3-T	TO-220F	G	D	S	Tube
5N60L-x-TF1-T	5N60G-x-TF1-T	TO-220F1	G	D	S	Tube
5N60L-x-TM3-T	5N60G-x-TM3-T	TO-251	G	D	S	Tube
5N60L-x-TN3-T	5N60G-x-TN3-T	TO-252	G	D	S	Tube
5N60L-x-TN3-R	5N60G-x-TN3-R	TO-252	G	D	S	Tape Reel

5N60L-x-TA3-T
(1)Packing Type
(2)Package Type
(3)Drain-Source Voltage
(4)Lead Free

(1) R: Tape Reel, T: Tube
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1
TM3: TO-251, TN3: TO-252
(3) A: 600V, B: 650V
(4) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25℃ unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage	5N60-A	V_{DSS}	600	V
	5N60-B		650	
Gate-Source Voltage		V_{GSS}	±30	V
Avalanche Current (Note 2)		I_{AR}	4.5	A
Continuous Drain Current		I_D	4.5	A
Pulsed Drain Current (Note 2)		I_{DM}	18	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	210	mJ
	Repetitive (Note 2)	E_{AR}	10	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	P_D	100	W
	TO-220F/TO-220F1		36	
	TO-251 / TO-252		54	
Junction Temperature		T_J	+150	℃
Operation Temperature		T_{OPR}	-55 ~ +150	℃
Storage Temperature		T_{STG}	-55 ~ +150	℃

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Pulse width limited by $T_{J(MAX)}$
3. L = 18.9mH, I_{AS} = 4.5 A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25℃
4. I_{SD} ≤ 4.5A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25℃

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction-to-Ambient	TO-220	θ_{JA}	62.5	°C/W
	TO-220F/TO-220F1		62.5	
	TO-251 / TO-252		160	
Junction-to-Case	TO-220	θ_{JC}	1.25	°C/W
	TO-220F/TO-220F1		3.47	
	TO-251 / TO-252		2.3	

■ ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	5N60-A	BV_{DSS}	V_{GS} =0V, I_D = 250μA	600			V
	5N60-B		V_{GS} =0V, I_D = 250μA	650			
Drain-Source Leakage Current		I_{DSS}	V_{DS} =600V, V_{GS} = 0V			1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS} =30V, V_{DS} = 0V			100	nA
	Reverse		V_{GS} =-30V, V_{DS} = 0V			-100	
Breakdown Voltage Temperature Coefficient		$\triangle BV_{DSS}/\triangle T_J$	I_D =250μA, Referenced to 25℃		0.6		V/℃
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS} =V_{GS}, I_D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS} =10V, I_D = 2.25A		2.0	2.5	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz		515	670	pF
Output Capacitance		C_{OSS}			55	72	pF
Reverse Transfer Capacitance		C_{RSS}			6.5	8.5	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	V_{DD} = 300V, I_D =4.5 A, R_G = 25Ω (Note 1, 2)		10	30	ns
Turn-On Rise Time		t_R			42	90	ns
Turn-Off Delay Time		$t_{D(OFF)}$			38	85	ns
Turn-Off Fall Time		t_F			46	100	ns
Total Gate Charge		Q_G	V_{DS} = 480 V, I_D = 4.5A, V_{GS} = 10 V (Note 1, 2)		15	19	nC
Gate-Source Charge		Q_{GS}			2.5		nC
Gate-Drain Charge		Q_{GD}			6.6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V_{SD}	V_{GS} = 0 V, I_S = 4.5 A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S				4.5	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				18	A
Reverse Recovery Time		t_{RR}	V_{GS} = 0 V, I_S = 4.5 A, d_{IF} / dt = 100 A/μs (Note 1)		300		ns
Reverse Recovery Charge		Q_{RR}			2.2		μC

Note 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

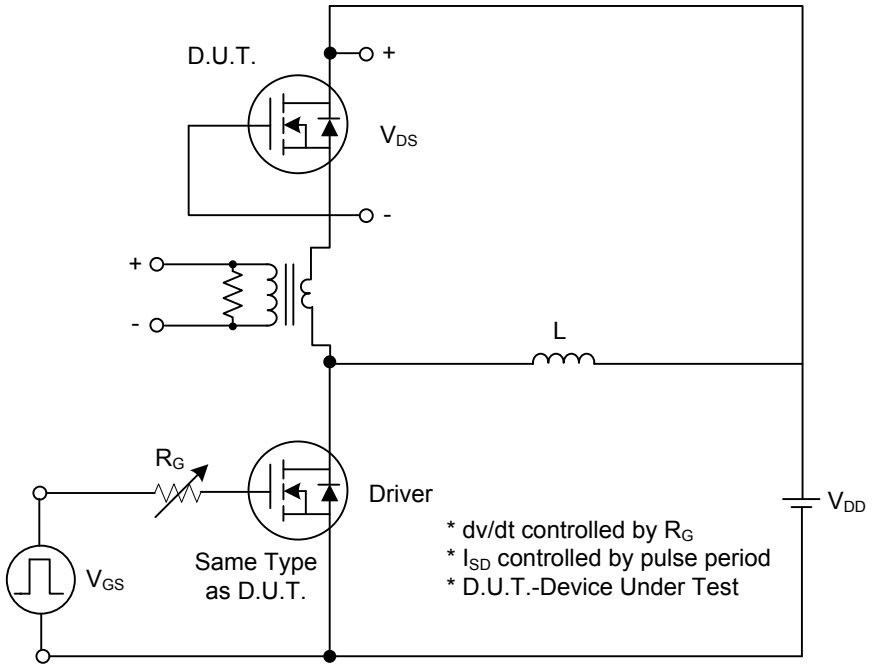


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

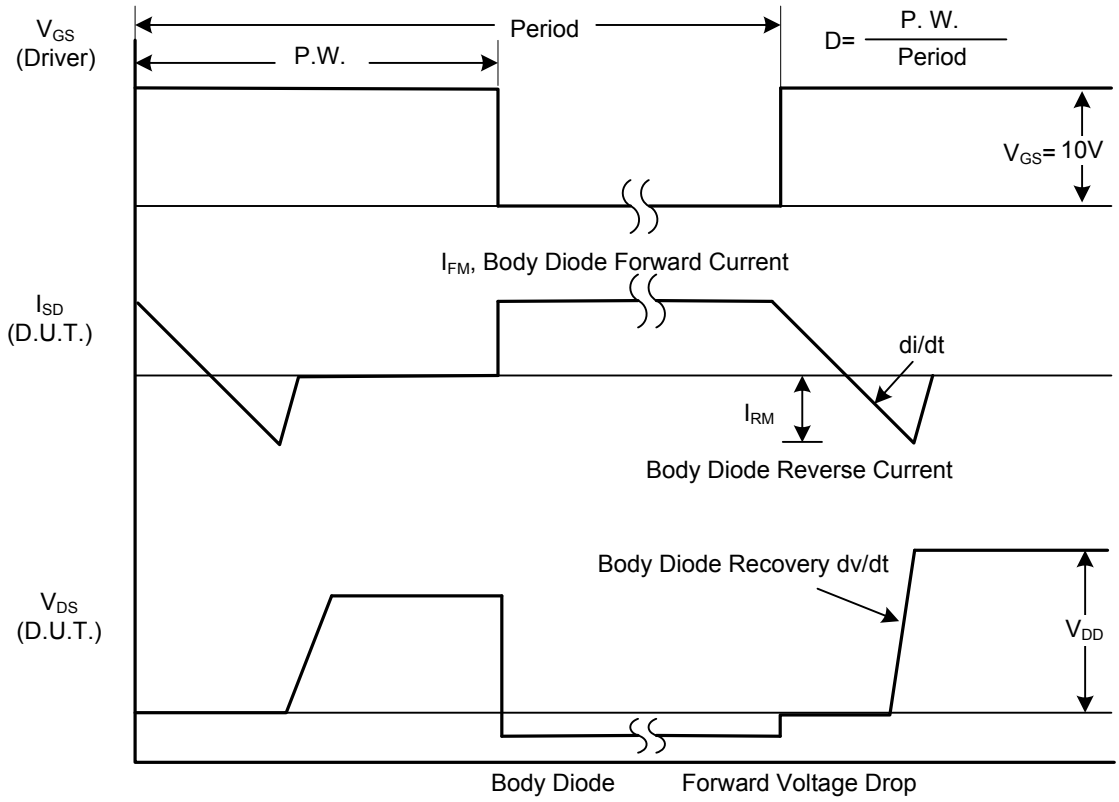


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

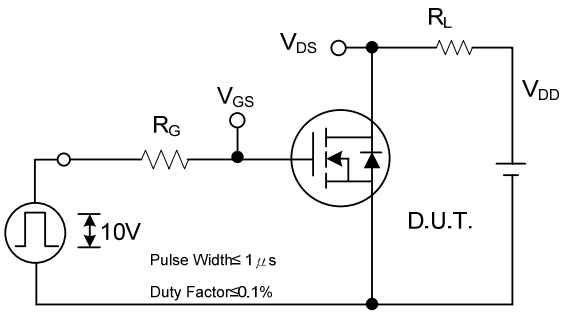


Fig. 2A Switching Test Circuit

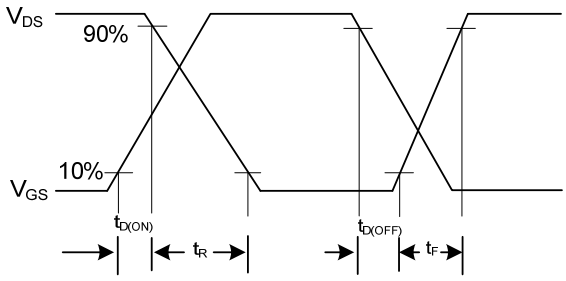


Fig. 2B Switching Waveforms

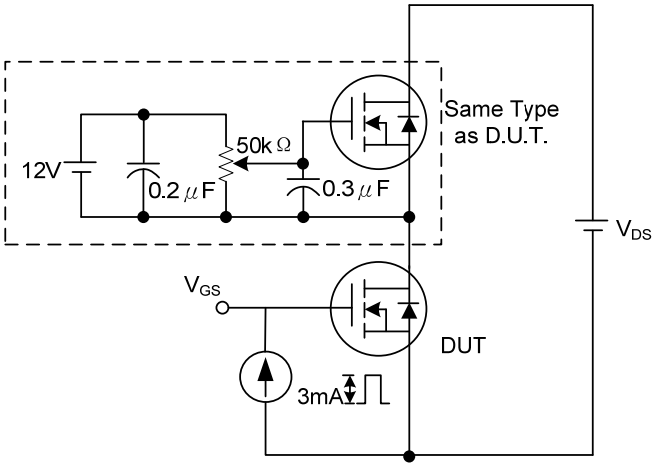


Fig. 3A Gate Charge Test Circuit

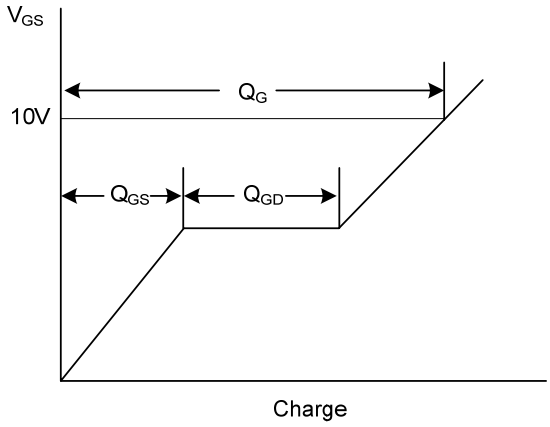


Fig. 3B Gate Charge Waveform

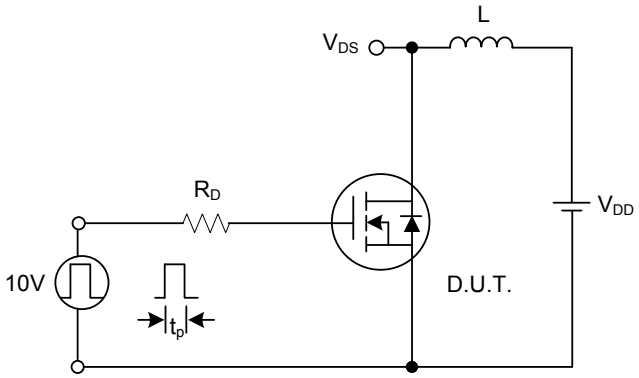


Fig. 4A Unclamped Inductive Switching Test Circuit

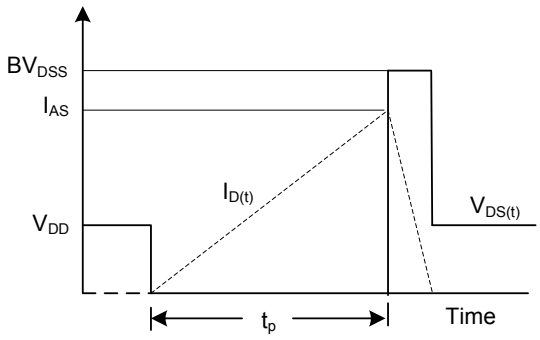


Fig. 4B Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS